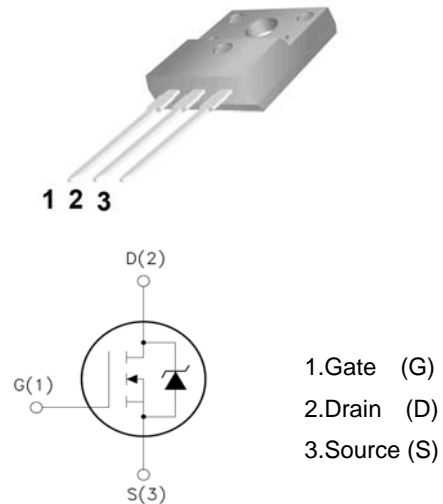


### General Description:

4N70, the silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-220F, which accords with the RoHS standard.

$V_{DSS}$	700	V
$I_D$	4	A
$P_D(T_C=25^\circ\text{C})$	30	W
$R_{DS(ON)Typ}$	2.55	$\Omega$

### TO-220F



### Features:

- **Fast Switching**
- **Low ON Resistance** ( $R_{dson} \leq 3.0\Omega$ )
- **Low Gate Charge** (Typical Data: 12.7nC)
- **Low Reverse transfer capacitances** (Typical: 2.7pF)
- **100% Single Pulse avalanche energy Test**

### Applications:

Power switch circuit of adaptor and charger.

**Absolute** ( $T_c = 25^\circ\text{C}$  unless otherwise specified):

Symbol	Parameter	Rating	Units
$V_{DSS}$	Drain-to-Source Voltage	700	V
$I_D$	Continuous Drain Current	4	A
	Continuous Drain Current $T_C = 100^\circ\text{C}$	2.5	A
$I_{DM}^{a1}$	Pulsed Drain Current	28	A
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$	V
$E_{AS}^{a2}$	Single Pulse Avalanche Energy	196	mJ
$dv/dt^{a3}$	Peak Diode Recovery $dv/dt$	5.0	V/ns
$P_D$	Power Dissipation	30	W
	Derating Factor above $25^\circ\text{C}$	0.24	W/ $^\circ\text{C}$
$T_J, T_{stg}$	Operating Junction and Storage Temperature Range	150, $-55$ to $150$	$^\circ\text{C}$
$T_L$	Maximum Temperature for Soldering	300	$^\circ\text{C}$

**Electrical Characteristics** ( $T_c = 25^\circ\text{C}$  unless otherwise specified):

<b>OFF Characteristics</b>						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$V_{DSS}$	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	700	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	$I_D=250\mu A, \text{Reference } 25^\circ\text{C}$	--	0.7	--	V/°C
$I_{DSS}$	Drain to Source Leakage Current	$V_{DS}=700V, V_{GS}=0V, T_a=25^\circ\text{C}$	--	--	1	$\mu A$
		$V_{DS}=560V, V_{GS}=0V, T_a=125^\circ\text{C}$	--	--	100	$\mu A$
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+30V$	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-30V$	--	--	-100	nA

<b>ON Characteristics</b>						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=2A$	--	2.55	3.0	$\Omega$
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	--	4.0	V
Pulse width $t_p \leq 300\mu s, \delta \leq 2\%$						

<b>Dynamic Characteristics</b>						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$g_{fs}$	Forward Transconductance	$V_{DS}=15V, I_D=2A$	--	3.7	--	S
$C_{iss}$	Input Capacitance	$V_{GS}=0V, V_{DS}=25V, f=1.0\text{MHz}$	--	606	--	pF
$C_{oss}$	Output Capacitance		--	48	--	
$C_{rss}$	Reverse Transfer Capacitance		--	2.7	--	

<b>Resistive Switching Characteristics</b>						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=4A, V_{DD}=350V, R_G=10\Omega$	--	14	--	ns
$t_r$	Rise Time		--	15	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	30	--	
$t_f$	Fall Time		--	9	--	
$Q_g$	Total Gate Charge	$I_D=4A, V_{DD}=560V, V_{GS}=10V$	--	12.7	--	nC
$Q_{gs}$	Gate to Source Charge		--	3.0	--	
$Q_{gd}$	Gate to Drain ("Miller") Charge		--	5.1	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$I_S$	Continuous Source Current (Body Diode)		--	--	4	A
$I_{SM}$	Maximum Pulsed Current (Body Diode)		--	--	16	A
$V_{SD}$	Diode Forward Voltage	$I_S=4A, V_{GS}=0V$	--	--	1.5	V
$t_{rr}$	Reverse Recovery Time	$I_S=4A, T_j = 25^\circ C$ $dI_F/dt=100A/us,$ $V_{GS}=0V$	--	325.3	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	1470	--	nC
$I_{RRM}$	Reverse Recovery Current		--	9.0	--	A
Pulse width $t_p \leq 300 \mu s, \delta \leq 2\%$						

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Junction-to-Case	4.17	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	62.5	$^\circ C/W$

<sup>a1</sup>: Repetitive rating; pulse width limited by maximum junction temperature

<sup>a2</sup>:  $L=10mH, I_D=6.3A, Start T_j=25^\circ C$

<sup>a3</sup>:  $I_{SD}=4A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}, Start T_j=25^\circ C$

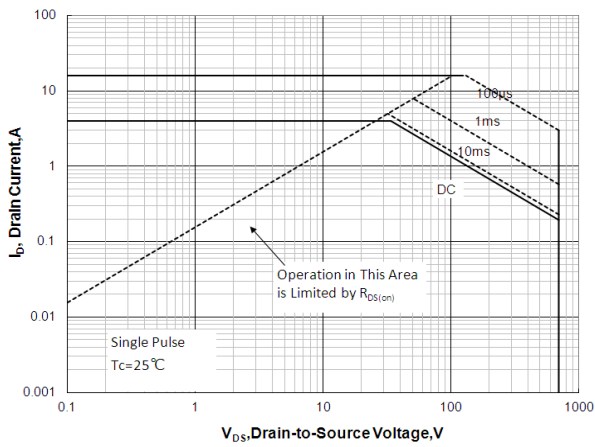
**Characteristics Curve:**


Figure 1 Maximum Forward Bias Safe Operating Area

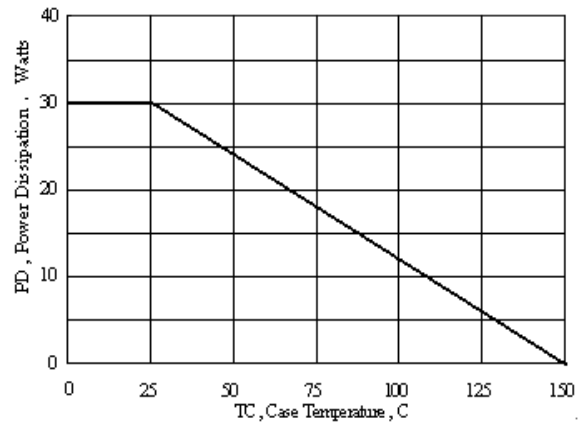


Figure 2 Maximum Power dissipation vs Case Temperature

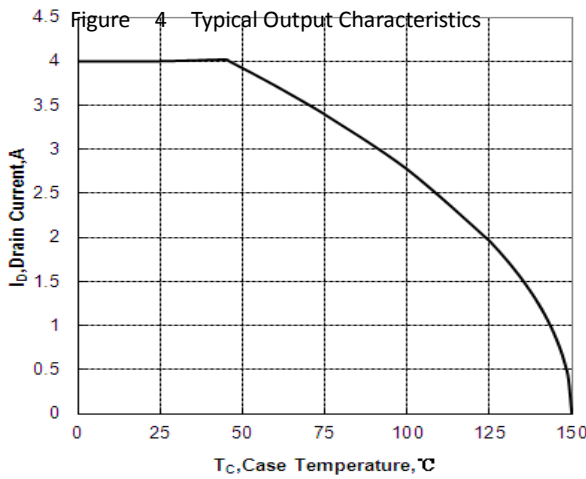


Figure 3 Maximum Continuous Drain Current vs Case Temperature

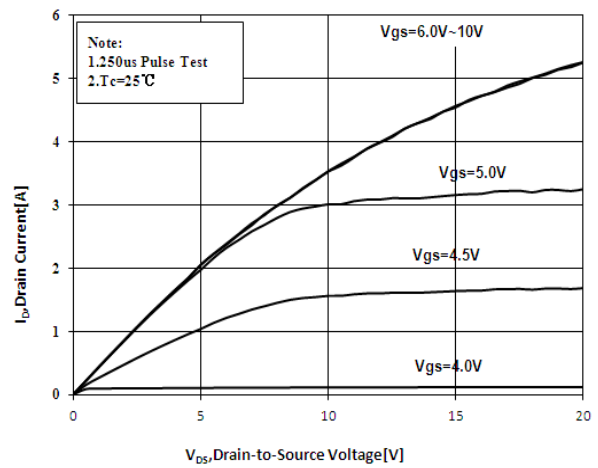


Figure 4 Typical Output Characteristics

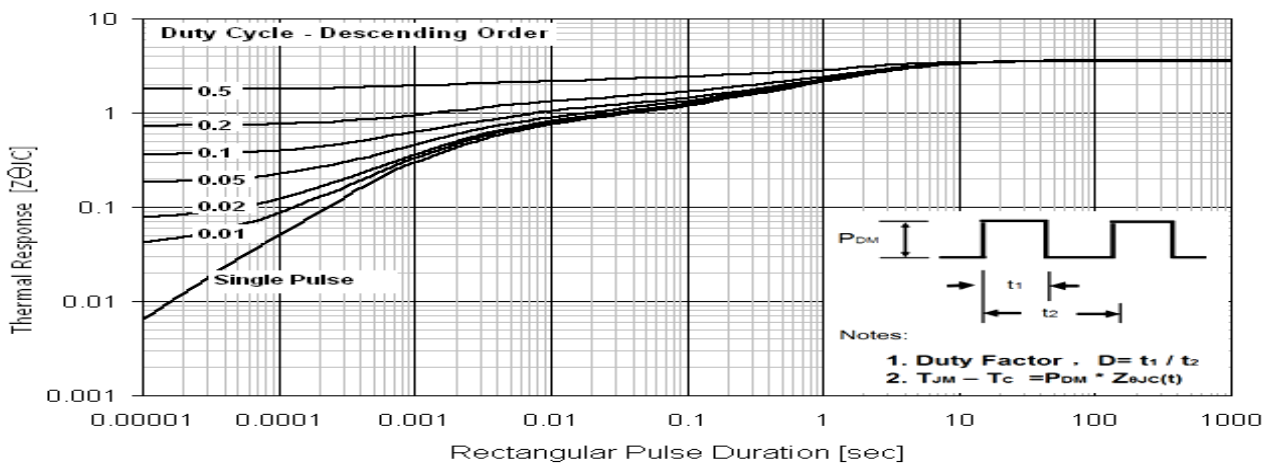


Figure 5 Maximum Effective Thermal Impedance , Junction to Case

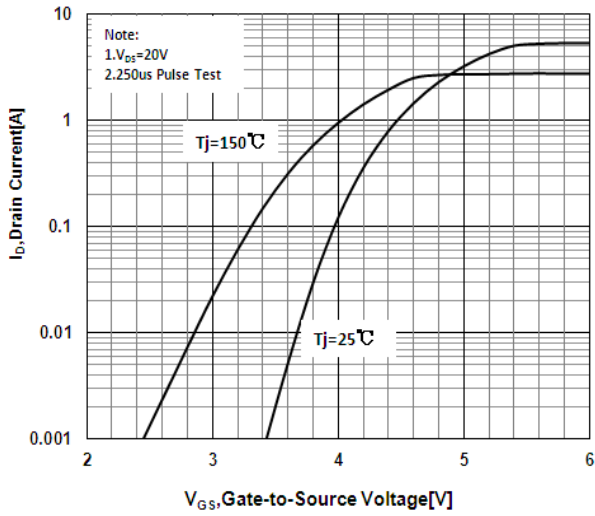


Figure 6 Typical Transfer Characteristics

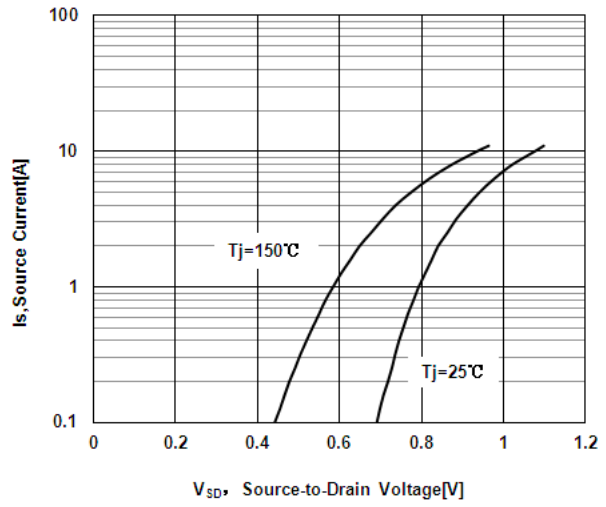


Figure 7 Typical Body Diode Transfer Characteristics

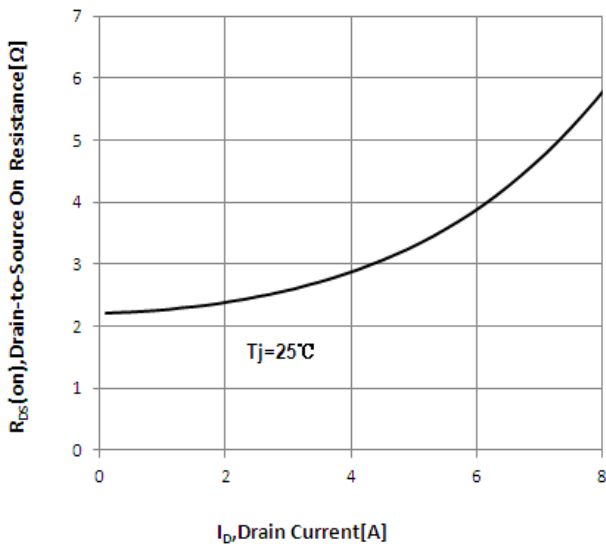


Figure 8 Typical Drain to Source ON Resistance vs Drain Current

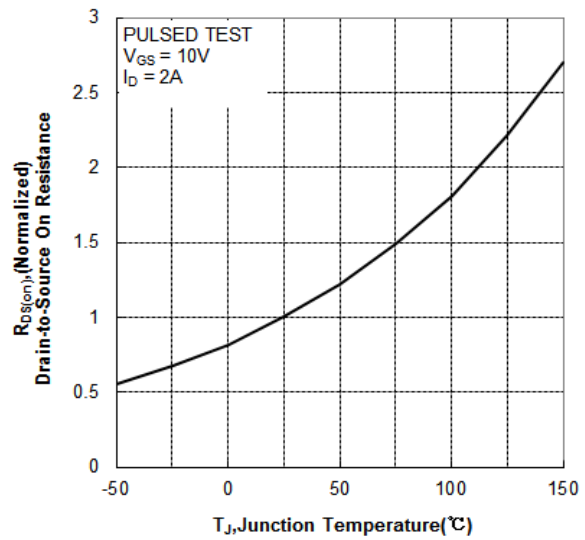


Figure 9 Typical Drain to Source on Resistance vs Junction Temperature

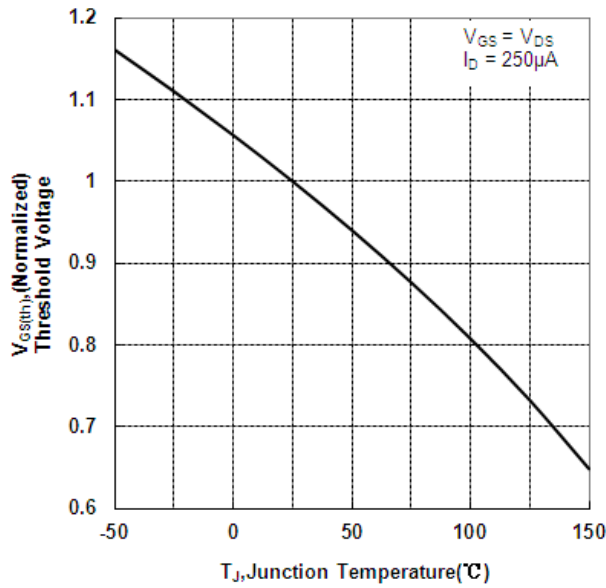


Figure 10 Typical Theshold Voltage vs Junction Temperature

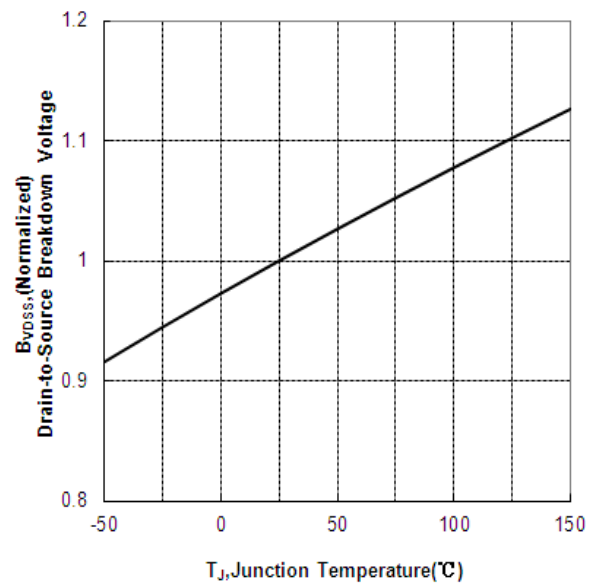


Figure 11 Typical Breakdown Voltage vs Junction Temperature

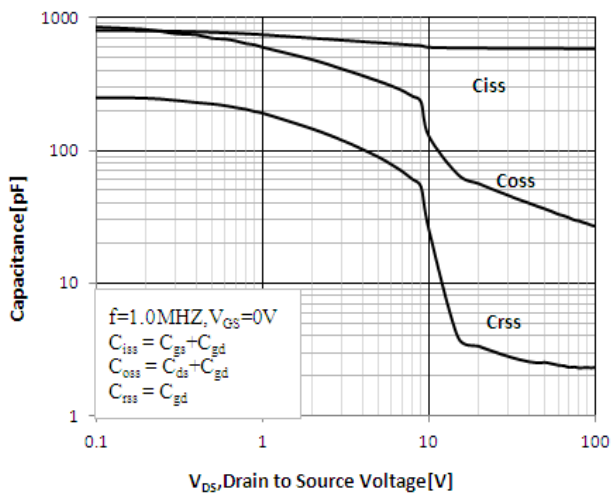


Figure 12 Typical Capacitance vs Drain to Source Voltage

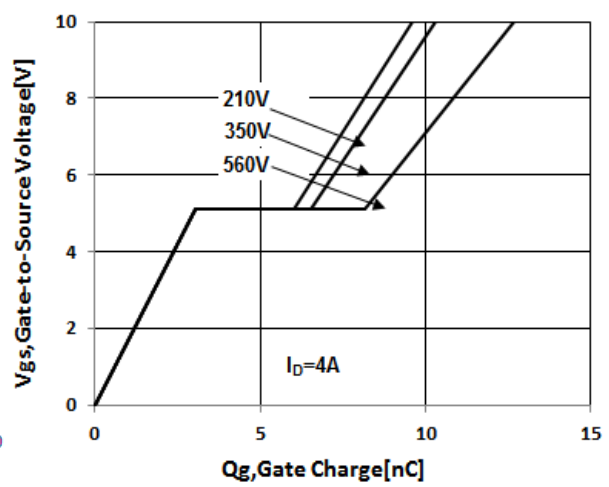


Figure 13 Typical Gate Charge vs Gate to Source Voltage

Test Circuit and Waveform

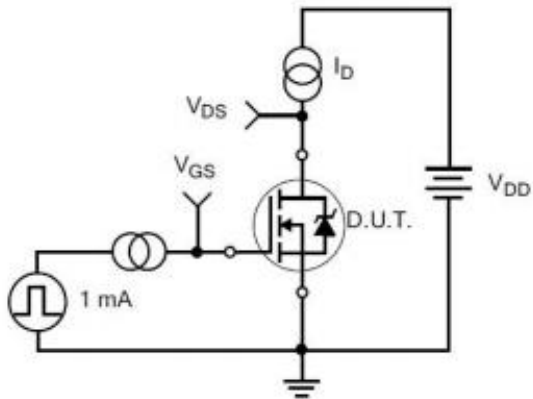


Figure 14. Gate Charge Test Circuit

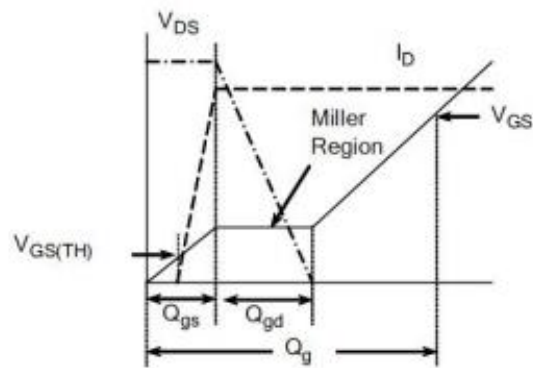


Figure 15. Gate Charge Waveforms

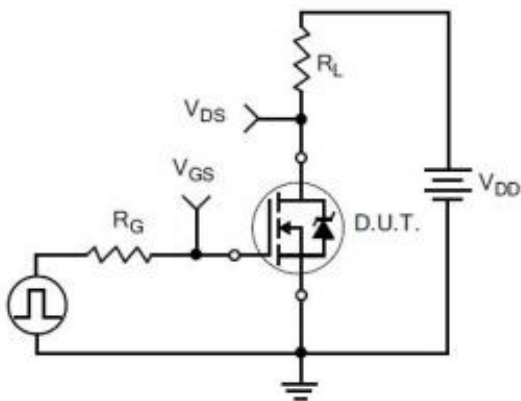


Figure 16. Resistive Switching Test Circuit

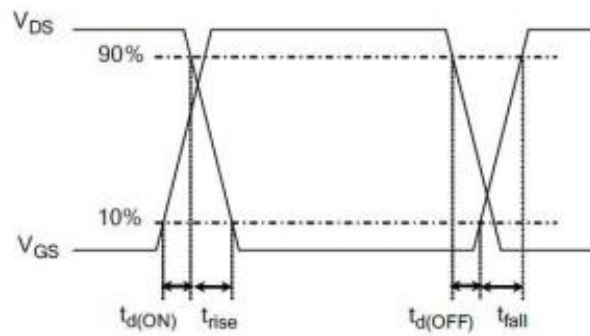


Figure 17. Resistive Switching Waveforms

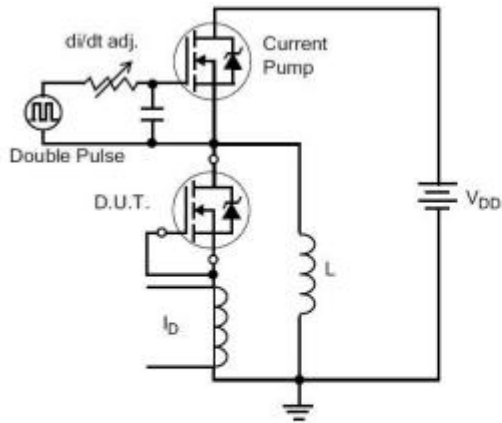


Figure 18. Diode Reverse Recovery Test Circuit

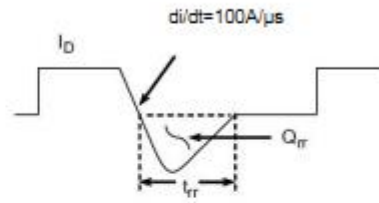


Figure 19. Diode Reverse Recovery Waveform

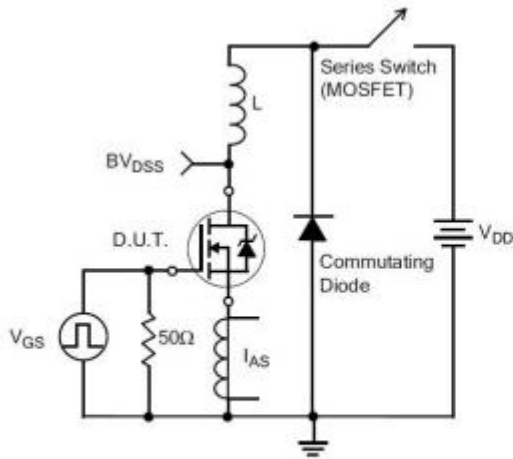


Figure 20. Unclamped Inductive Switching Test Circuit

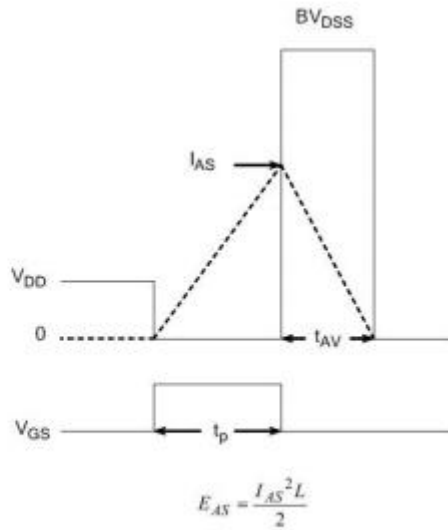
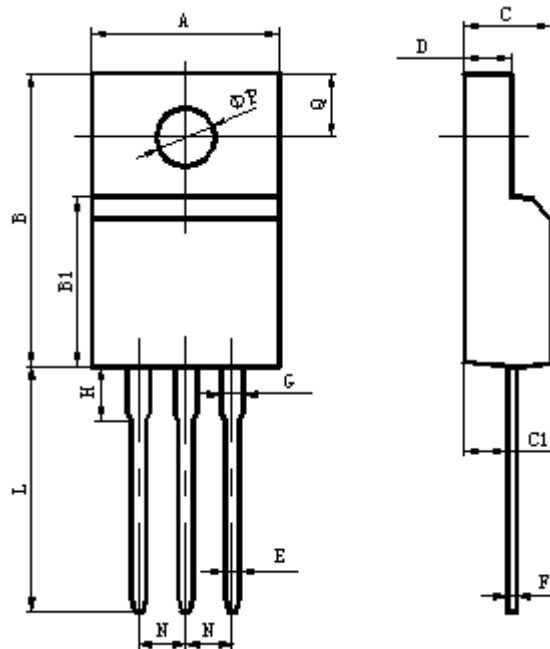


Figure 21. Unclamped Inductive Switching Waveform



**Package Information:**


Items	Values(mm)	
	MIN	MAX
A	9.60	10.4
B	15.4	16.2
B1	8.90	9.50
C	4.30	4.90
C1	2.10	3.00
D	2.40	3.00
E	0.60	1.00
F	0.30	0.60
G	1.12	1.42
H	3.40	3.80
	1.60	2.90
L*	12.0	14.0
N	2.34	2.74
Q	3.15	3.55
Φ P	2.90	3.30

\*:adjustable

**TO-220F** Package